

Fig. 1. (a) GISAXS contour plot showing the time evolution of the in-plane scattering profile for InN growth at 320 °C. An individual intensity profile at 160 growth cycles is superimposed below, demonstrating the fitting of the correlation peak, from which the island center-to-center spacing and areal density are determined. (b) Extracted island center-to-center spacings and areal densities as functions of the number of growth cycles, for InN growth at 180°C, 250°C, and 320 °C.

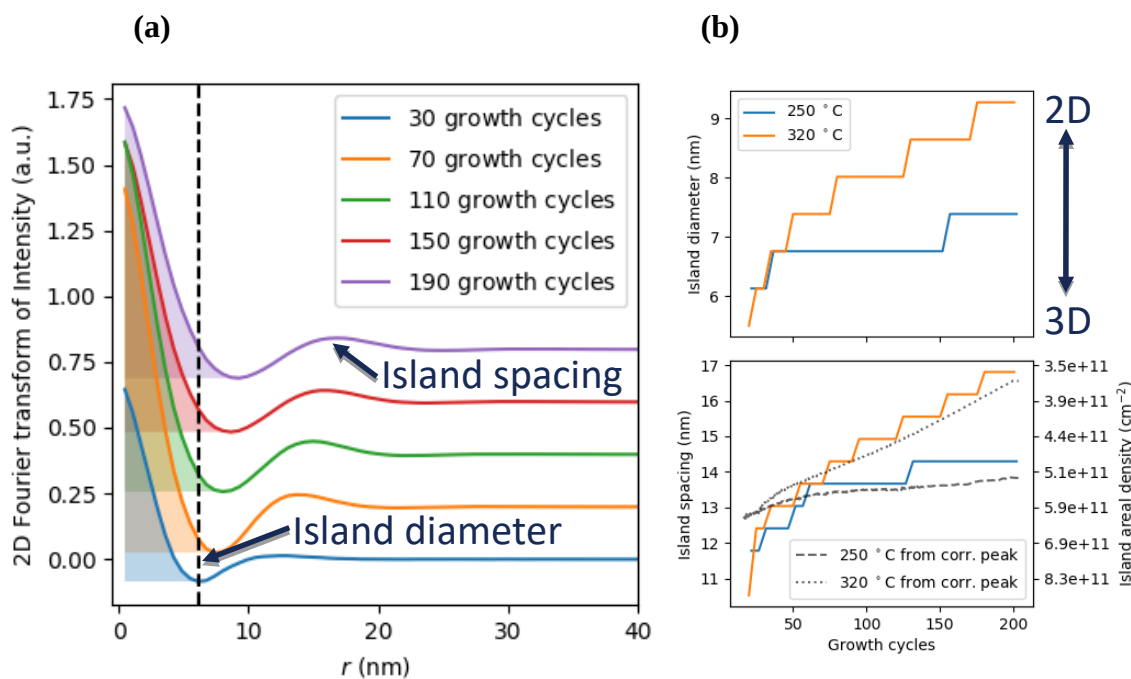


Fig. 2. (a) 2D Fourier transforms of the GISAXS intensity profile for InN growth at 320 °C. The island diameter and center-to-center spacing increase with the number of growth cycles. (b) Comparison of island characteristics extracted from Fourier analysis for growth of InN at 250 °C and 320 °C. The similarity of the film thicknesses but significant difference in island diameter implies that the higher temperature growth is comparatively more two-dimensional.